

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	963	257/528,531.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 09:10
S2	1212	361/761,763,764.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 09:13
S3	2167	S1 or S2	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 09:14
S4	1	S3 and (negative near capacitanc\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 09:22
S5	1	10/650395	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 09:19
S6	676	negative near capacitanc\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 09:23
S7	657	S3 and inductor\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 11:04
S8	2167	S3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 09:30
S9	678	S3 and transistor\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 09:31
S10	296	S7 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 10:48
S11	1	S3 and (PHEMTS or gallium adj arsenide adj pseudomorphic adj high-electron adj mobility adj transistors)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 10:59
S12	2169	S3 or (gallium adj arsenide adj pseudomorphic adj high-electron adj mobility adj transistors)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/26 17:48

S13	0	S3 and (gallium adj arsenide adj pseudomorphic adj high-electron adj mobility adj transistors)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 11:01
S14	255	S3 and ((gallium adj arsenide)or GaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 11:02
S15	163	S14 and S7	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/16 11:04
S16	2	"6124624".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/19 08:39
S17	2	"6385019".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/19 10:15
S18	0	2002EP-0207642504-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/26 17:49
S19	0	EP-0207642504-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/26 17:49
S20	1	2002EP-0207642504	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/09/26 18:04